

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	10/655179	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 06:15
S2	1345	(257/640,649,760).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 06:15
S3	3668	(438/257,724,744,754,757,769, 791,954).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 06:44
S4	171	((silicon near nitride) Si\$1N\$1) with reduc\$3 near3 hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:00
S5	25	S4 and ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:09
S6	0	S4 with ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:10
S7	0	S4 same ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:10
S8	2673	((silicon near nitride) Si\$1N\$1) with ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:11
S9	1666	((silicon near nitride) Si\$1N\$1) near5 ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:11

S10	1167	S9 and memory near3 cell	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:13
S11	0	S10 and charge near3 storage with reduc\$3 near hydrogen near2 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:14
S12	908	reduc\$3 near hydrogen near2 content	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:14
S13	0	(reduc\$3 near hydrogen near2 content) with charge near stor\$3 near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:17
S14	15	(reduc\$3 near hydrogen near2 content) with silicon near nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:18
S15	0	(reduc\$3 near hydrogen near2 content) with silicon near nitride with ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:18
S16	0	(reduc\$3 near hydrogen near2 content) with (silicon near nitride) with ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:18
S17	2673	((silicon near nitride) Si\$1N\$1) with ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:19
S18	1666	((silicon near nitride) Si\$1N\$1) near5 ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:20
S19	1250	((silicon near nitride) Si\$1N\$1) near3 ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:20

S20	889	((silicon near nitride) Si\$1N\$1) near2 ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:20
S21	152	((silicon near nitride) Si\$1N\$1) near ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:20
S22	0	S21 and chrg\$ near3 stor\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 08:21
S23	81	S21 and charge near3 stor\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 14:59
S24	9772	"Si3N4"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 09:12
S25	0	"Si3N4" near5 charg\$3 near stor\$4 near layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 09:13
S26	2	"Si3N4" near5 charg\$3 near stor\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 09:13
S27	307	(257/354).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/01/18 15:00
S28	0	S27 and ((silicon near nitride) Si\$1N\$1) with reduc\$3 near3 hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:49
S29	41	S27 and (ONO (silicon near oxide near5 silicon near nitride near5 silicon near oxide))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:15

S30	1	S29 and reduc\$3 near3 hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:03
S31	1	S29 and charg\$3 near storage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:11
S32	1	S27 and ONO	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:13
S33	40	S29 and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:44
S34	20	S33 and charge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:17
S35	2	S33 and charge near3 storage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:46
S36	266	S27 not S29	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:45
S37	4	S36 and charge near3 storage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:46
S38	91	S36 and ((silicon near nitride) Si\$1N\$1)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:54
S39	31	S36 and ((silicon near nitride) Si\$1N\$1) and charge	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:18

S40	2	S36 and ((silicon near nitride) Si\$1N\$1) and charge near storage	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 15:55
S41	9934	charge near3 (strap\$4 trap\$4 nitride)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:18
S42	323586	sonos monos mnos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:19
S43	1326	S41 and S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:20
S44	323586	15same S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:20
S45	674	S41 same S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:21
S46	480	S41 with S42	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:21
S47	97389	ono	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:21
S48	285	S46 and S47	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:21
S49	856613	hydrogen	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:22

S50	24	S48 and S49	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:22
S51	290	S49 near5 atomic:adj:percent\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:25
S52	1	S48 and S51	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:25
S53	14781	S49 near5 percent\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:25
S54	1	S48 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/01/18 16:25